

POST-IRRADIATION STRESS-STRAIN AND FRACTURE RESPONSE EVOLUTION DESCRIPTION OF RPV STEELS: RECENT AND FUTURE DEVELOPMENTS

7TH SEPTEMBER 2018

Contribution to SOTERIA WP5

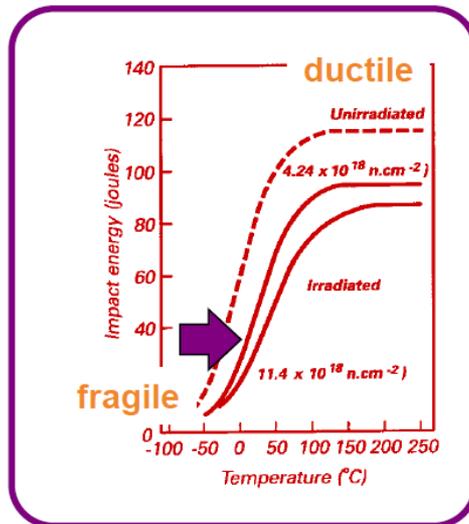
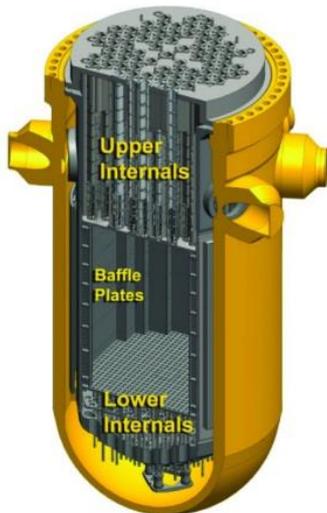
Co-workers: B. Marini, P. Forget, K. Singh, L. Vincent, Y. Li

Speaker: **Christian Robertson**

Long-term goal or vision: predicting dose-dependent fracture toughness response based on non-destructive post-irradiation examinations (material polycrystalline microstructures, i.e. grain sizes and orientations; irradiation defect microstructures) and physically based models

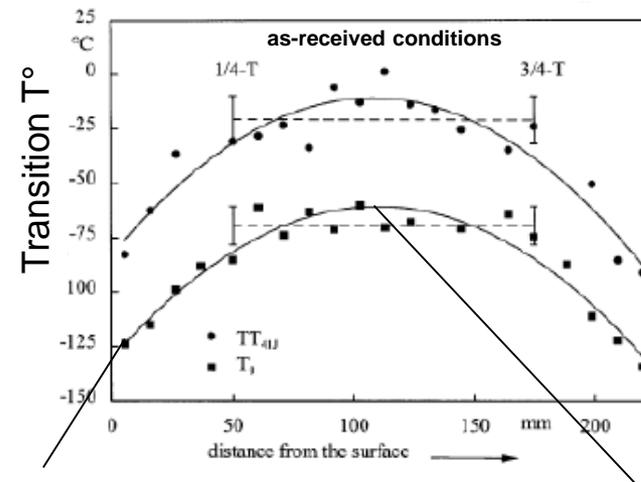
☞ minimizing/optimizing time-consuming/costly mechanical testing of post-irradiated specimens in hot cells

Thick-walled components: microstructure and fracture toughness variability



Initial microstructural variations: a major contributing factor

H.V. Viehrig et al. Nucl. Engi. Des. 212 (2002) 115-124



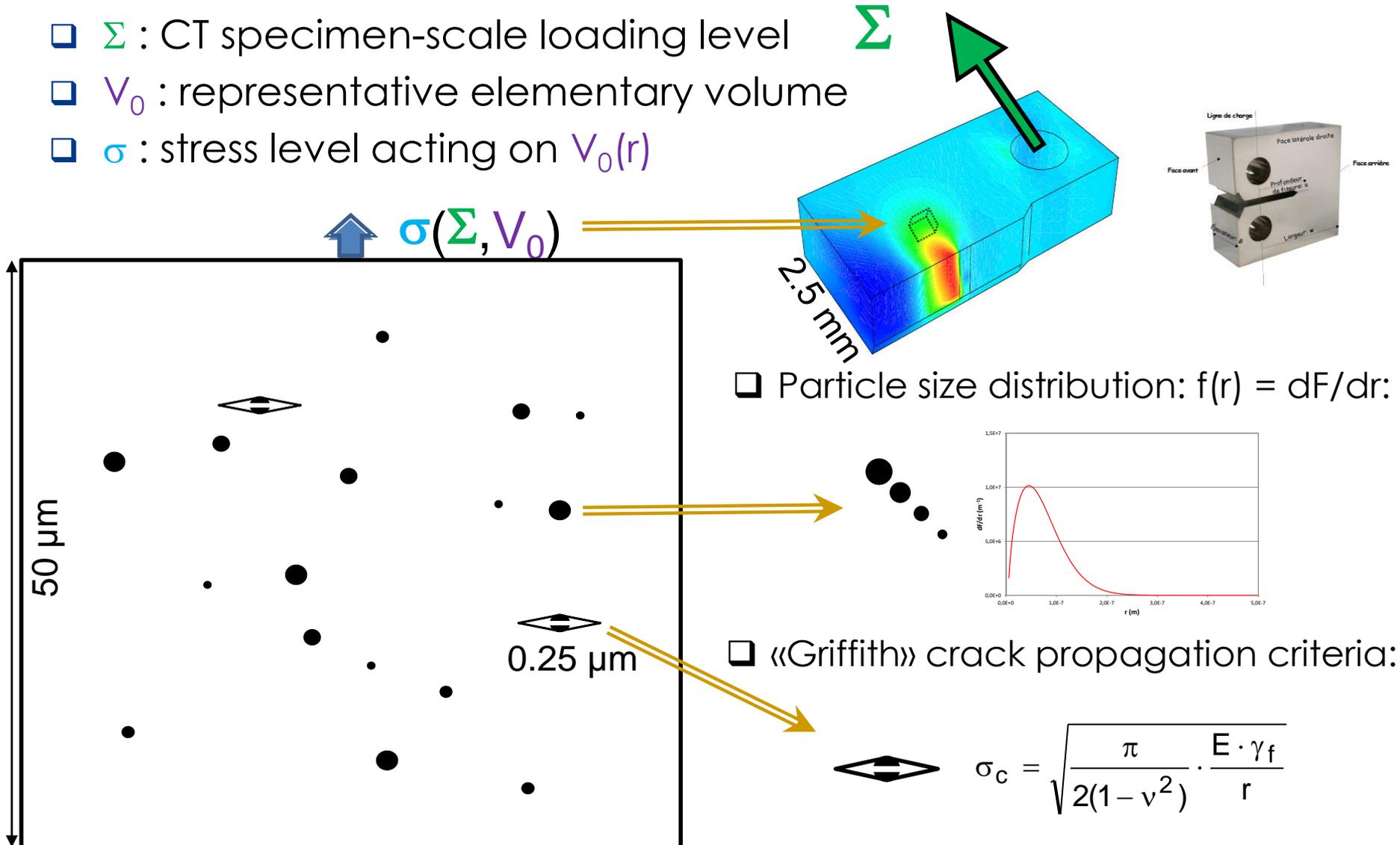
outer surface

center

☞ Modelling efforts addressing: dose-dependent fracture response and its scattering

«Local Brittle Fracture models»

- Σ : CT specimen-scale loading level
- V_0 : representative elementary volume
- σ : stress level acting on $V_0(r)$

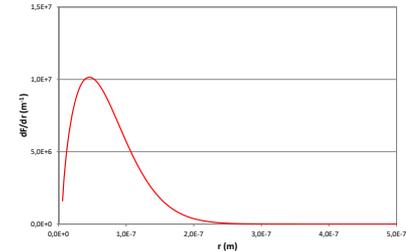
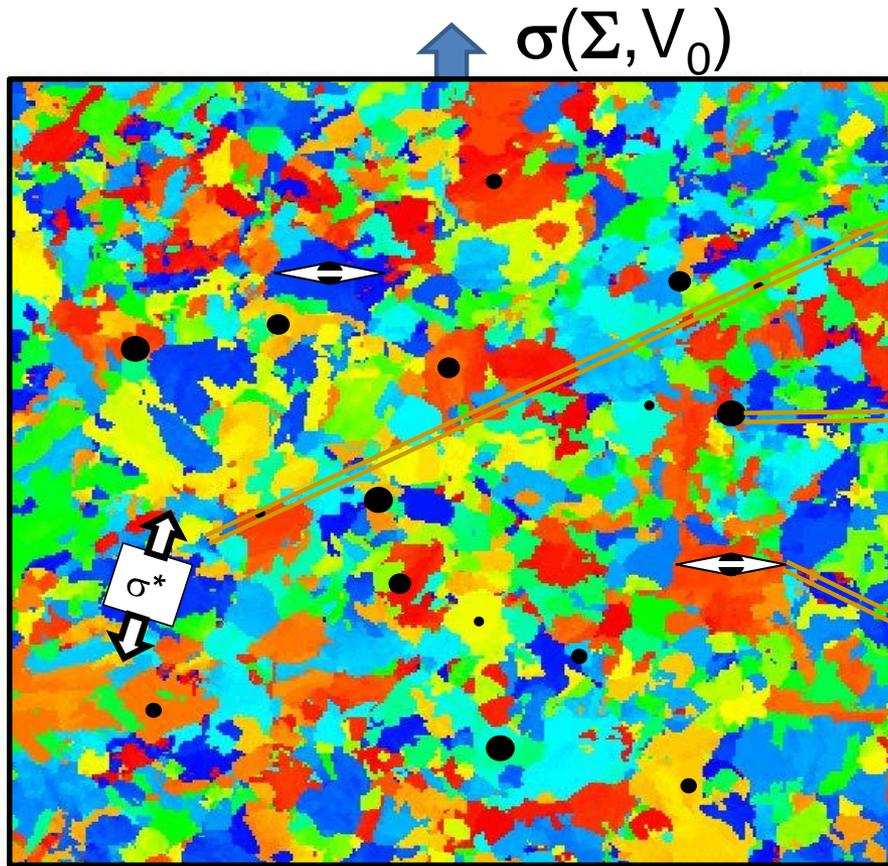


...including local stress distribution (MIBF)

➤ **MIBF model INPUTS** : irradiation-induced hardening level, particle size distribution, surface energy, grain-size, grain orientation, grain-scale stress fields

J. Nucl. Mat. 406 (2010) 91-96

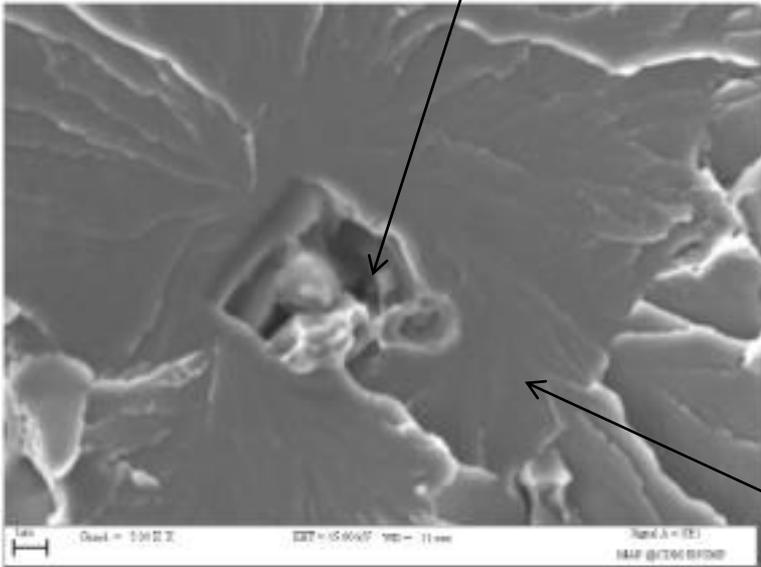
RPV steel microstructure
⇒ local stress distribution σ^* inside V_0



$$\sigma_c = \sqrt{\frac{\pi}{2(1-\nu^2)} \cdot \frac{E \cdot \gamma_f}{r}}$$

Weakest link assumption

Cracked inclusion: brittle fracture initiator

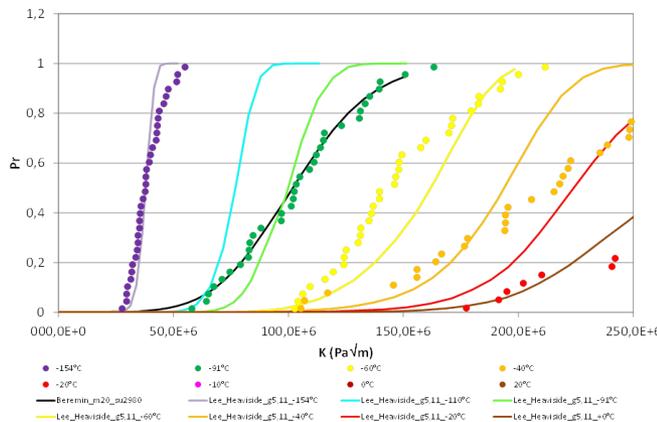


Weakest link assumption

- I- all inclusions/particles break down, for $\epsilon > \epsilon_{p0}$
- II- micro-cracks grow (or not) according to a definite criteria
- III- first micro-crack develops \rightarrow the whole specimen fails
- IV- **fracture toughness then directly relates to plastic zone size a_0 , near the micro-crack initiators**

Cleavage fracture surface

Failure probability



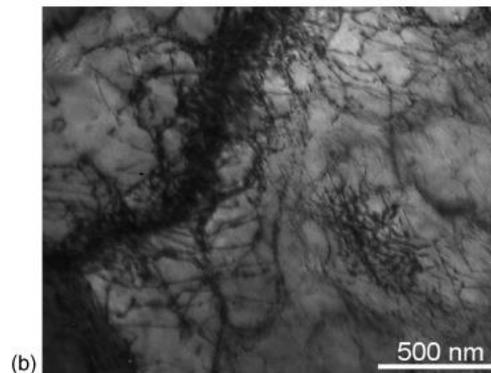
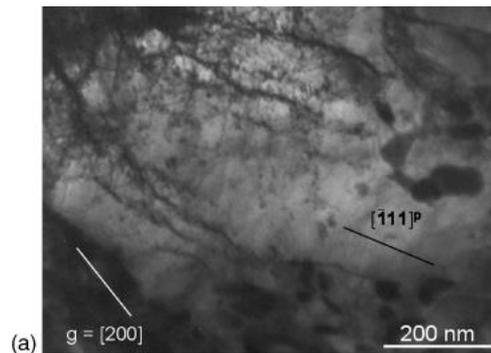
Transition curves, DBT shift

load

Micro-crack induced plastic zone?

- Q. Effect of straining temperature on a_0 ?
- Q. Grain size and orientation effect on a_0 ?
- Q. Dose effect, irradiation temperature effect, on a_0 ?

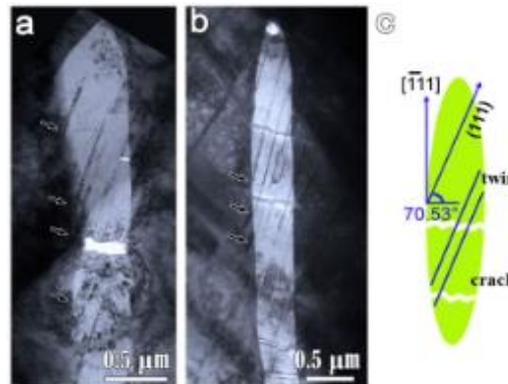
R. Crack-induced plasticity: dislocation-mediated



Modelling Simul. Mater. Sci. Eng. **18** (2010) 025003

☞ «Statistical, investigation of post-irradiation plasticity mechanisms using, 3D DD simulations»

☞ Dislocation Dynamics simulations?



MnS in steel, Sci. Reports 4, 5118 (2014)

Dislocation dynamics simulations?



« TRIDIS » code

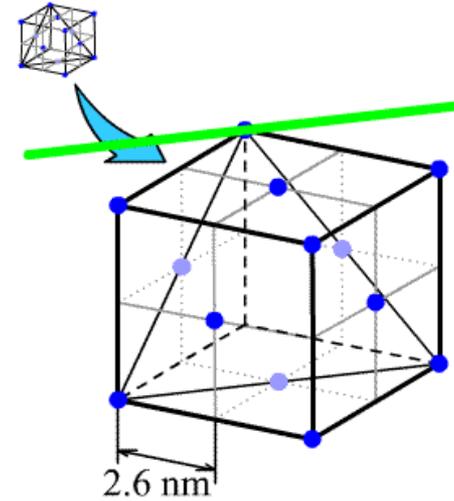
Model. Simul. Mater. Sci. Eng. 6 (1998) 755-770

Dislocation Model

Discrete dislocation lines

Discrete time steps: 10^{-10} s

Discrete bcc lattice



Stress

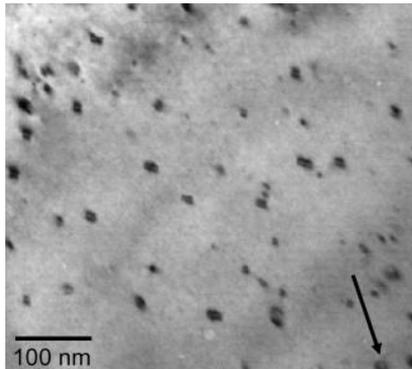
Dislocation Dynamics
code

Dislocation microstructures

Plastic strain

Dislocation theory

- Dislocation mobility (stress and T° dependent)
- Interaction with radiation defects, other dislocations, GB...
- Cross-slip



FCC models (Cu, FCC Fe)

Screw ~ Edge

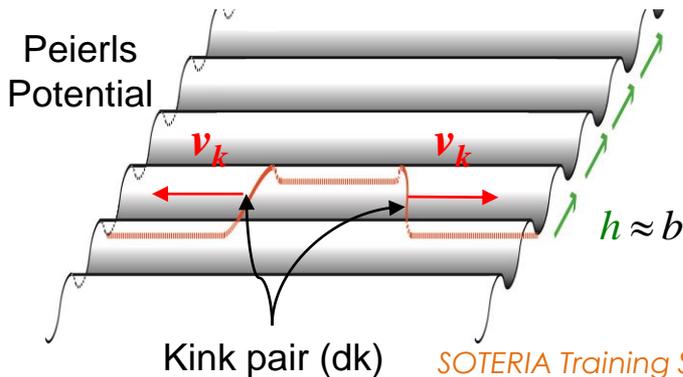
Negligible Peierls barrier ($\tau_p \sim 10$ MPa)



Phonon-drag mechanism

$$v_{screw}(\tau) = v_{edge}(\tau) = \frac{\tau b}{B}$$

- τ : applied stress $\gg \tau_p$
- B : Viscous drag coefficient
- b : Burgers vector module
- τ_p : Peierls Stress



BCC Fe and Fe alloys

Screw \neq Edge

Velocity anisotropy depends on T°

Low temperature

High temperature

Significant Peierls barrier ($\tau_p \sim 1$ GPa)



Thermally activated mobility

$$v_{screw}(\tau, T) \ll v_{edge}(\tau) = \frac{\tau b}{B}$$

Athermal regime

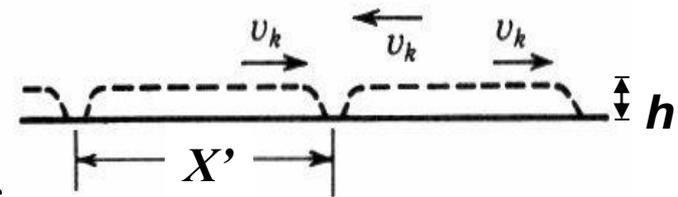
$$v_{screw} \approx v_{edge}$$

Low-T screw dislocation mobility mechanism

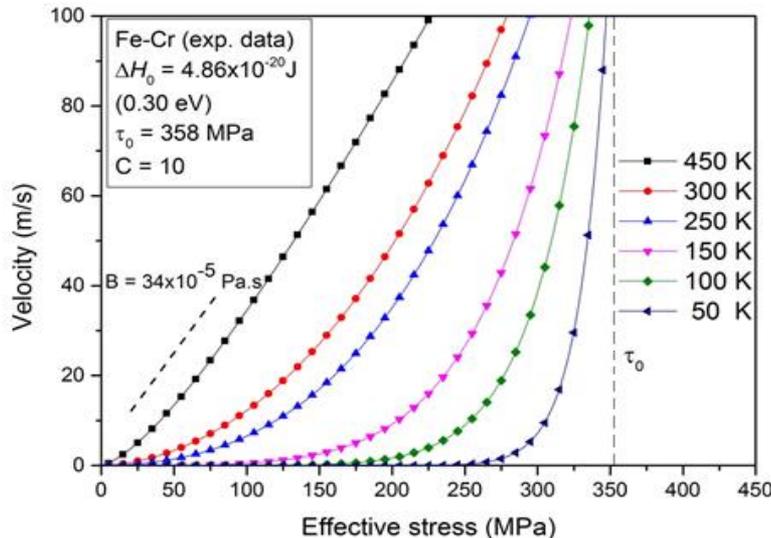
- **Nucleation** of a kink pairs (thermally activated)
- Kink pair **propagation** $v_k \propto \tau$ « effective » $B_k < B_{edge}$

Journal of Nuclear Materials 504 (2018) 84-93

$$v_{screw} = hJX'$$



- h : distance between Peierls valleys
- J [$\text{m}^{-1}\text{s}^{-1}$] : kink pair **nucleation rate** per unit length
- X' [m] : kp **mean free path** before annihilation with another dk [increases with kink velocity (v_k) and decreases with J]



$$v_{screw}(\tau^*, T) = \underbrace{\frac{8\pi b(\tau^*)^2}{\mu B h}}_{\text{Stress-dependent pre-factor}} X' \exp\left(-\frac{\Delta G(\tau^*, T)}{k_B T}\right)$$

Stress-dependent pre-factor

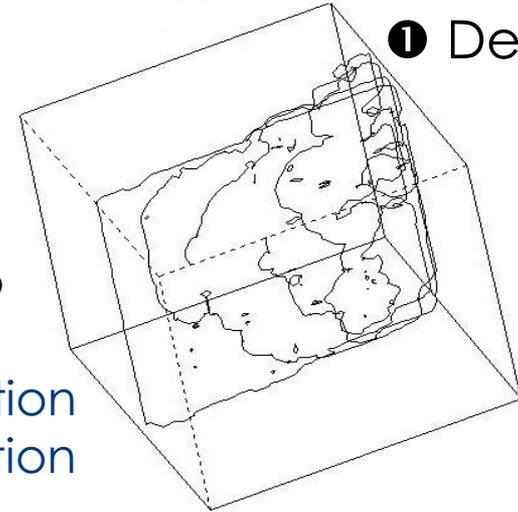
➡ Progressive transition from Low- T to Room- T

DD simulation setup

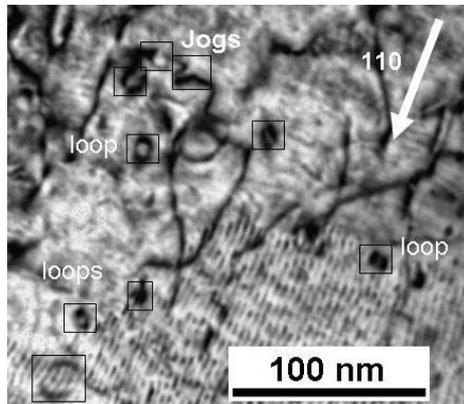
1 μm^3 ferritic grains (Fe-C or Fe-Cr):

- Defect number density and defect size depend on selected dose and T_{irr} condition
- Uni-axial tension, strain-rate controlled conditions, fixed straining T° , presence of cross-slip

- **Model INPUTS:** grain size, kink-pair activation energy, phonon drag coefficient, irradiation defect size, and number density

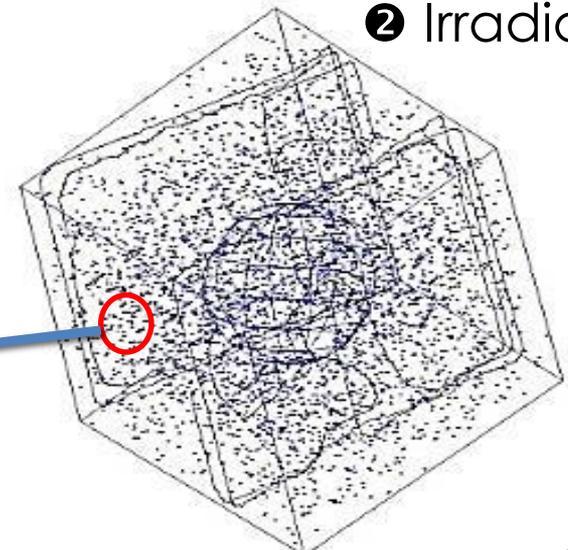
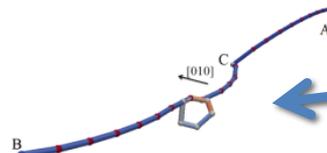


① Defect-free

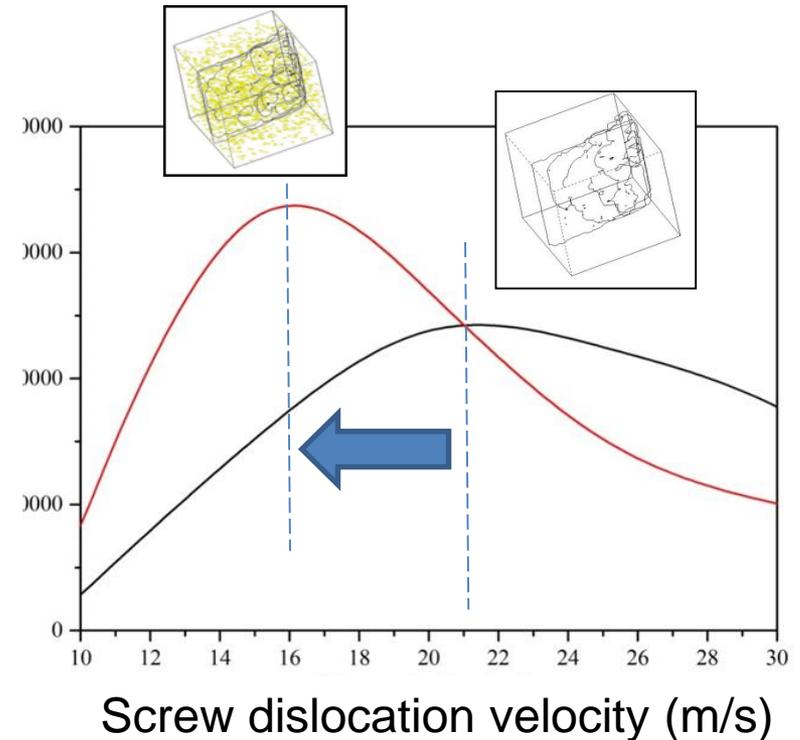
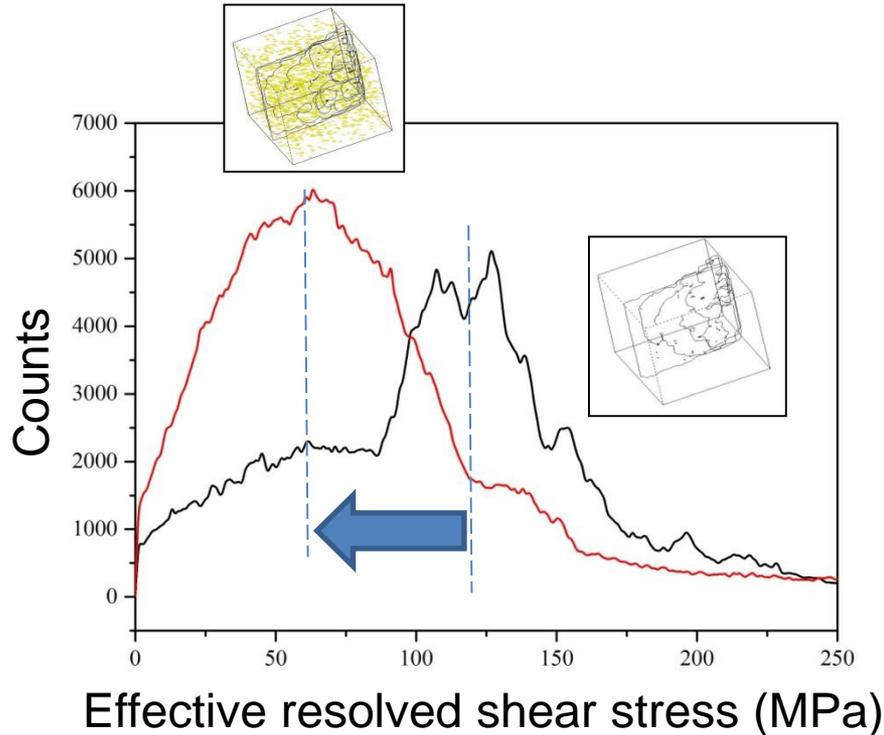


$T_{irr}=400^\circ\text{C}$, dose = 1 dpa, defect size $D = 50$ nm

dislocation/defect interactions

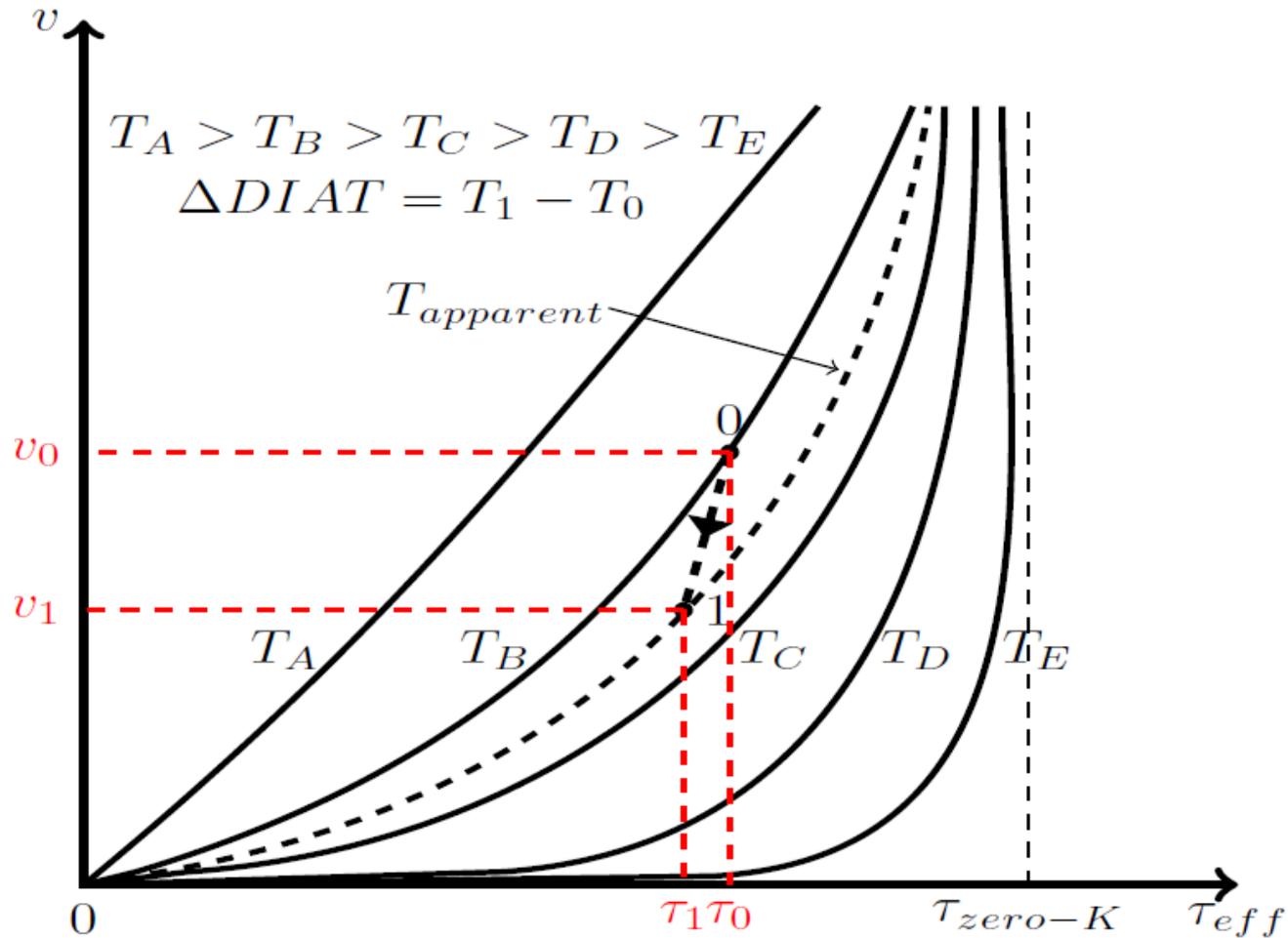


② Irradiated



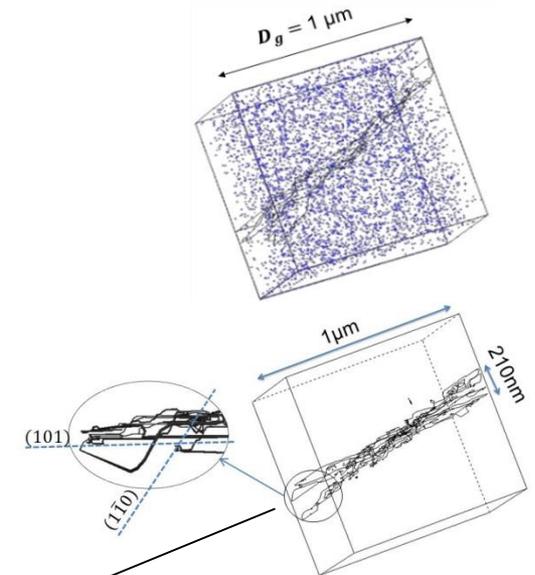
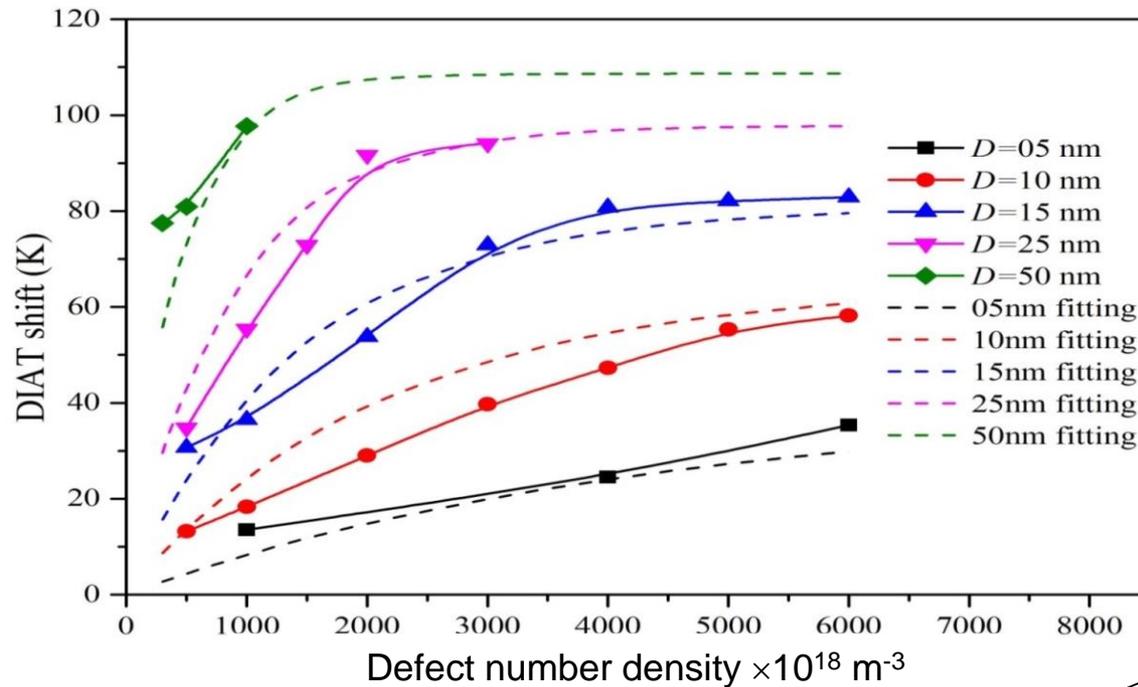
- Defect-induced effect on effective screw dislocation mobility :
 - **statistically significant.** Why it matters?

DIAT shift: interpretation



$T_{apparent} - T_0 =$ Defect-Induced Apparent straining Temperature shift ($\Delta DIAT$)

Δ DIAT: a systematical investigation



$$\Delta \text{DIAT} = \Delta T_{max} \left(1 - \exp\left(-\frac{D}{\lambda}\right) \right) \left(1 - \exp(-d^2 DN) \right) \approx \Delta \text{DBTT}$$

N : defect number density (in nm^{-3}); D : defect size (in nm);
3 material-dependent scaling parameters (ΔT_{max} , d and λ)

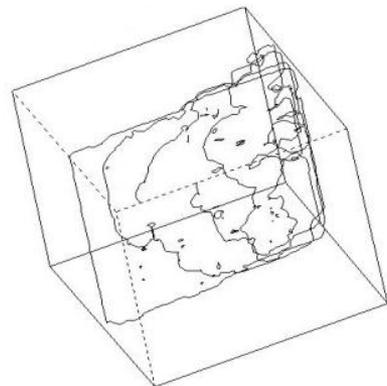
Δ DIAT: a simple, predictive DBT shift indicator



$$\Delta\text{DBTT} \approx \Delta\text{DIAT} = \Delta T_{max} M$$

ΔT_{max} → first principles
elasticity theory &
dislocation statistics

- ΔH_0 (Joules)
- τ_{Peierls} (MPa)
- μ (MPa)
- B (MPa.s)
- T_0 (K)
- [n] and D at saturation
- effective τ_1 (Orowan)
- effective τ_0 (at $T_0 = 300\text{K}$)**
- No adjustable variable/parameters



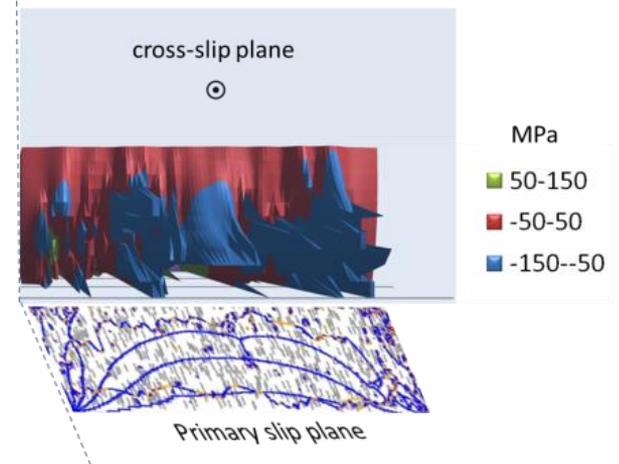
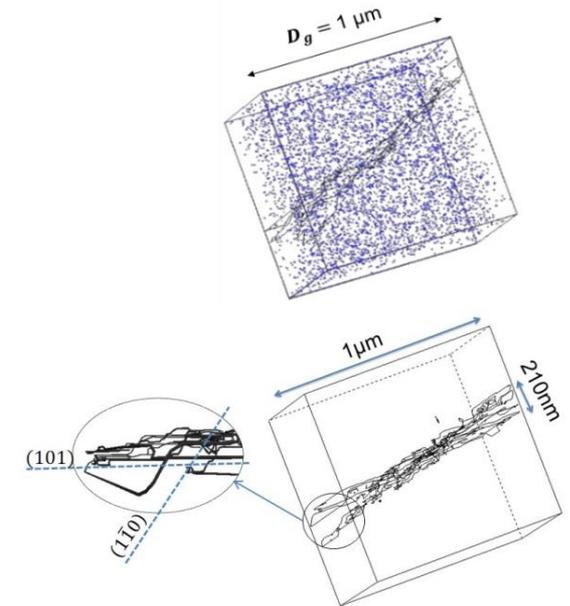
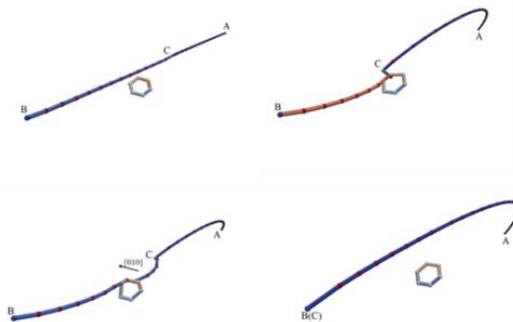
$0 < M < 1$:
dimensionless «mitigation» term



$M \propto$ «stress landscape» associated
with shear band structures



Controls cross-slip activity →
effective defect interaction strength
(τ^*) and dislocation length (X')



Δ DIAT: a simple, predictive DBT indicator



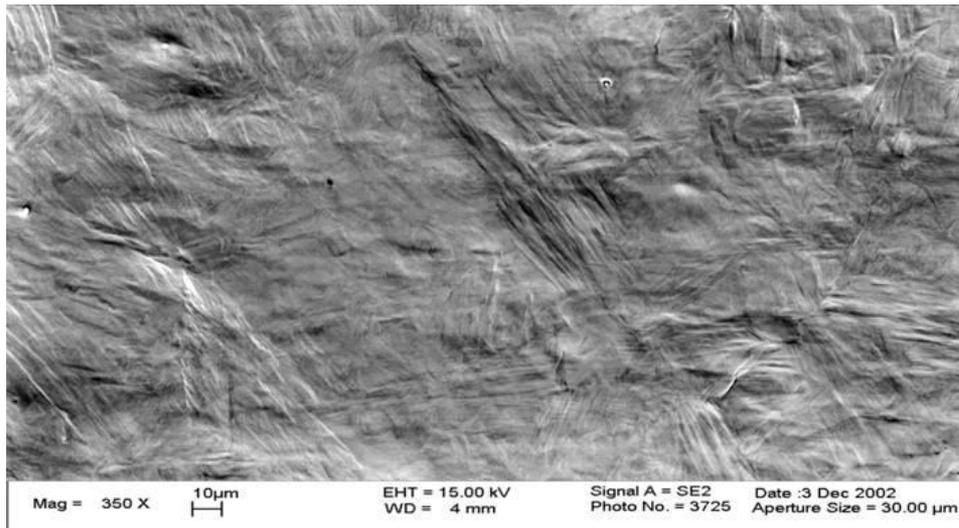
Stress landscape \leftrightarrow shear band spreading

- Grain size and grain orientation
- Dose-dependent τ_{YS} (MPa)
- Strain per shear band
- $[n]$ and D at considered dose, irradiation- T°
- Defect strength (MPa)
- Dislocation accumulation rate with ϵ_p**

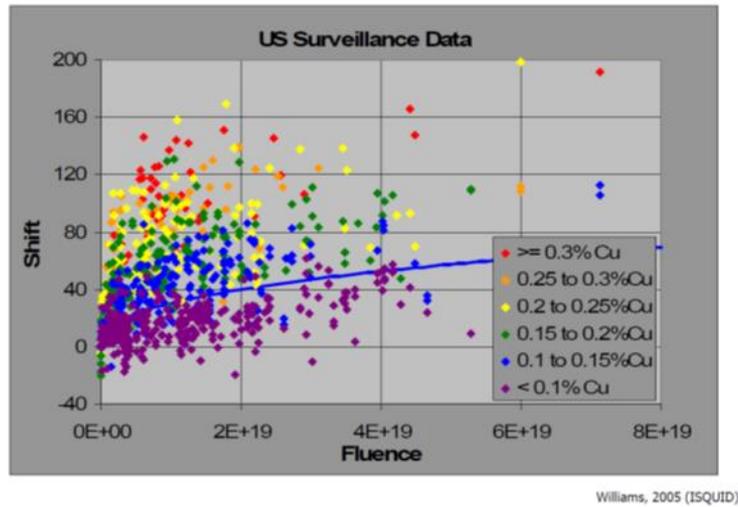
Shear band spacing and thickness: micro-model based on **DD simulation results**



Micro-model validation based on comparison with experimental observation of strained specimens



Dose-dependent DBT shift



Defect number density

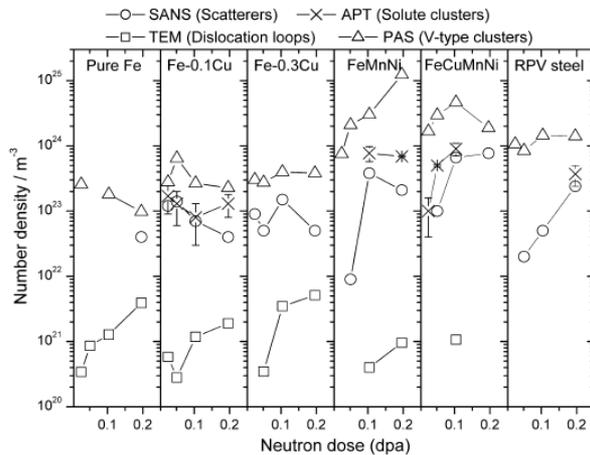
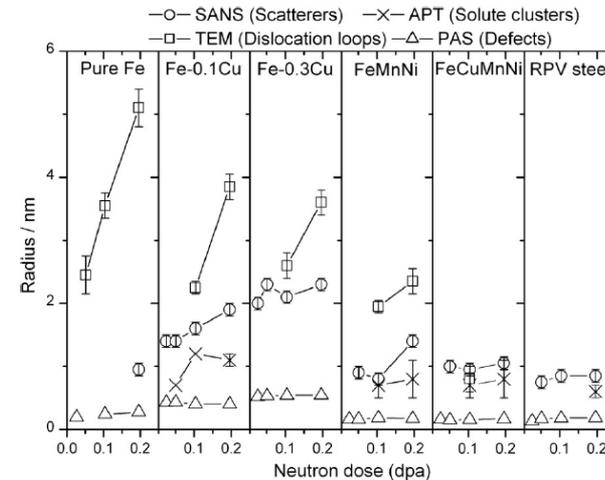
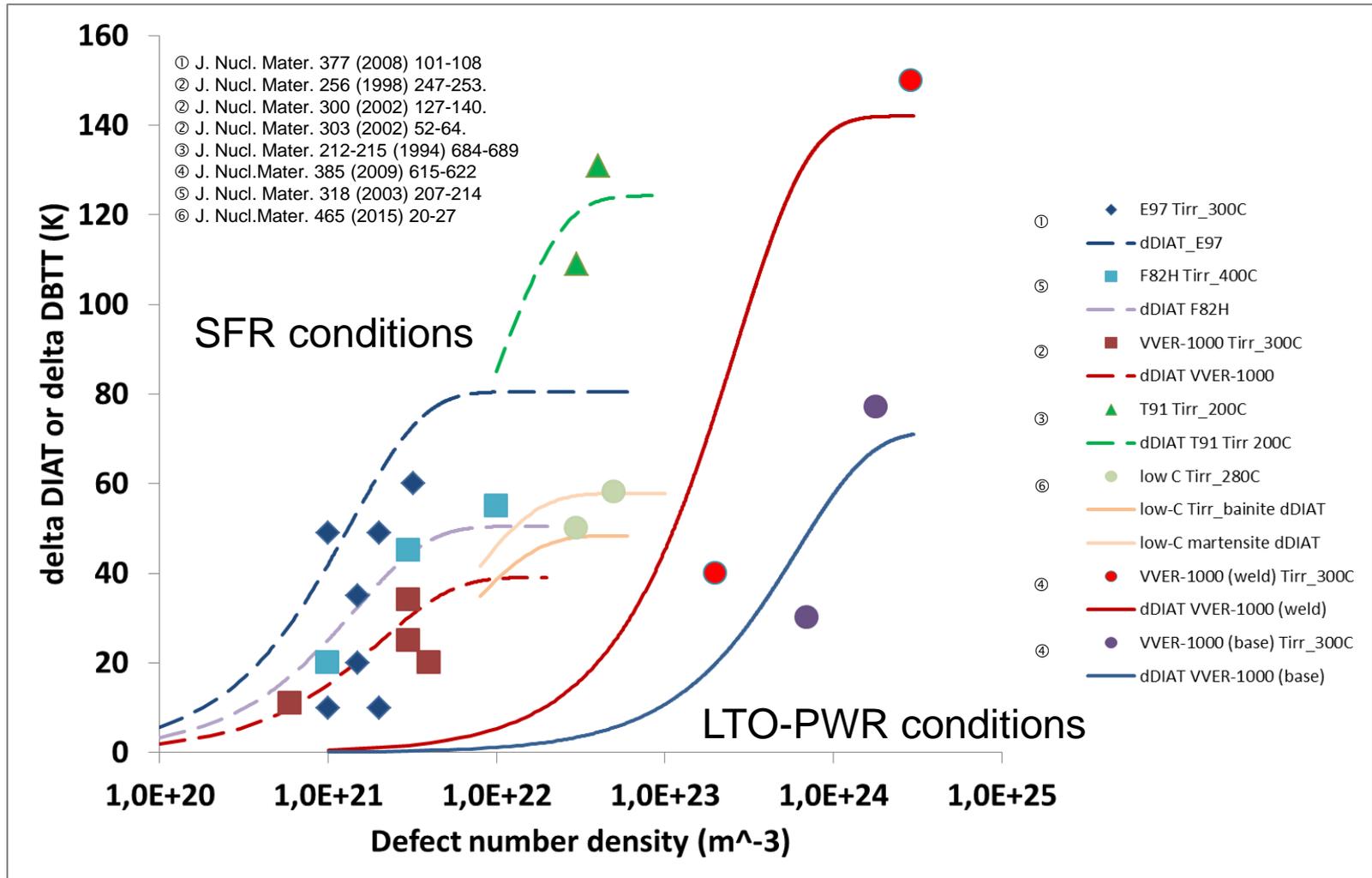


Fig. 3. Number density of radiation-induced damage as functions of dose from APT, SANS, TEM and PAS measurements.

Defect size



Δ DIAT/ Δ DBTT comparison

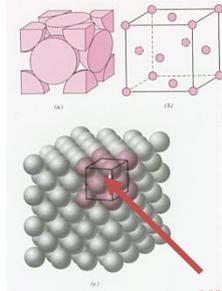
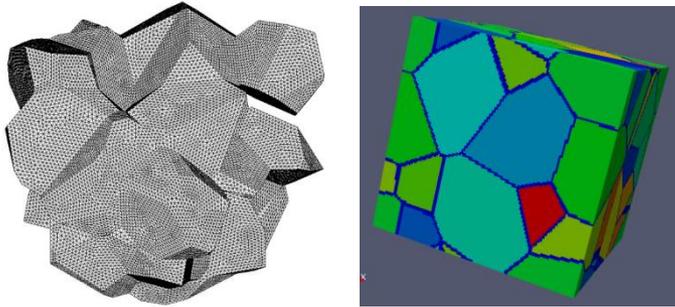


☞ Δ DIAT \approx Δ DBTT [irradiation conditions: little or no segregation at fracture initiators (particles or GB)]

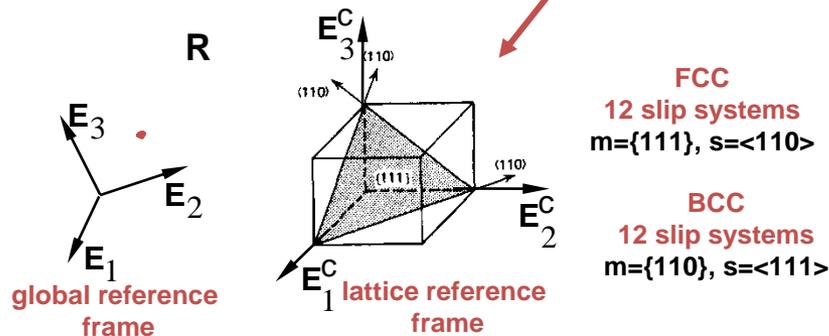
☞ Absolute toughness levels: link with local approach of fracture/MIBF approach/models

☞ Support/link dose-dependent crystal plasticity...

Crystal plasticity approach



unit cell



- ❑ Explicitly models discrete grains and slip systems, accounting for anisotropy of single crystal properties and crystallographic texture.
- ❑ Slip system level constitutive equations for dislocations with use of Internal state variables for various parameters at each slip system
- ❑ Approach used to study aggregate of crystals to obtain a better understanding of single-crystal or poly-crystal behavior.

➤ Support from DD-based simulations

- ❑ Physically based stress-velocity rules, system-system interaction strength
- ❑ Evolution of irradiation defect population with increasing strain, mobile dislocation density evolution

Modified T° -dependent mobility rule



$$\frac{1}{\dot{\gamma}_{total}} = \frac{1}{\dot{\gamma}_{nuc}} + \frac{1}{\dot{\gamma}_{prop}} \quad (1)$$

$\dot{\gamma}_{nuc}$ accounts for thermally activated kink pair nucleation. The stress-independent l_s term assumes that each nucleated kink-pair sweeps the whole dislocation line, while a given screw dislocation moves from one Peierls valley to the next one.

Inverse of strain rate sensitivity parameter

Reference shear strain rate

$$\dot{\gamma}_{prop1} = \dot{\gamma}_0 \left(\frac{\tau_{RSS}}{\tau_c} \right)^n$$

High value of n limits its numerical applicability

$$\dot{\gamma}_{prop2} = \rho_m b v_k = \rho_m b \cdot \frac{\tau_{eff} b}{B} \quad (2)$$

$$\dot{\gamma}_{nuc2} = \rho_m b \frac{8\pi\tau_{eff}^2}{\mu B} \exp \left[-\frac{\Delta H_0}{k_B T} \left(1 - \left[\frac{\tau_{eff}}{\tau_0} \right]^p \right)^q \right] X_\infty$$

$$X_\infty = 2\sqrt{\frac{v_k}{J}}$$

Formulations (1)&(2) yield comparable results at the strain rate 10^{-4} for $\Delta H_0 > 0.6$ eV

Formulation (2) is however able to handle a **larger range of strain rate and material parameters**.

It is also found to be more robust in terms of convergence in finite element formulation.

- τ_{eff} depends on many different contributions, including irradiation defects, acting as obstacles cutting the dislocation glide planes hence, treated as forest obstacles to the glide of dislocations.
- Dose level controls the number of loops N_{irr} formed and temperature controls the size of the loop d_{irr}

$$\rho_{irr} = N_{irr} d_{irr}$$

Irradiation defect density evolution

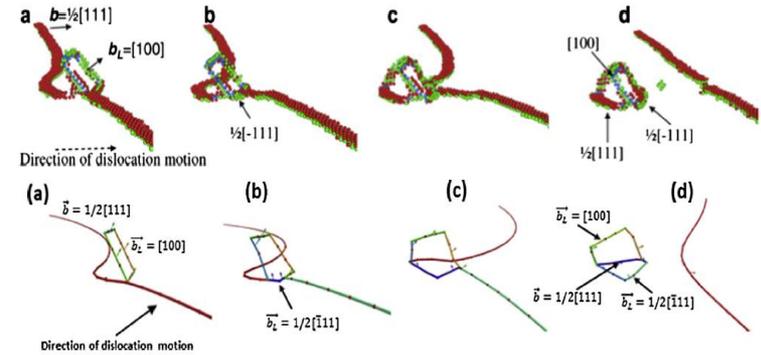
$$\dot{\rho}_{irr} = -\xi \rho_{irr} \dot{\gamma}$$

$0 < \xi < 1$: loop annihilation parameter

Affects τ_{eff} in eq. (2)

Through DD simulations → significant dose-dependent increase in total and mobile dislocation density.

This increase is ascribed to interaction of screw dislocations with irradiation defects → dislocation pinning, multiplication.



X.J. Shi et al. *J. Nucl. Mat.* 460 (2015) 37-43

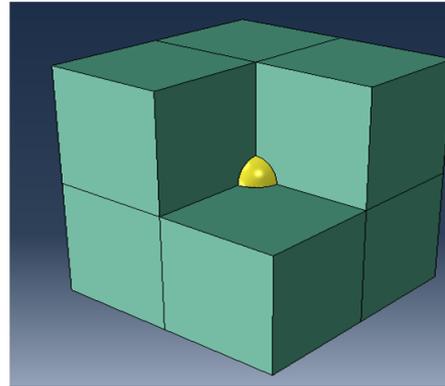
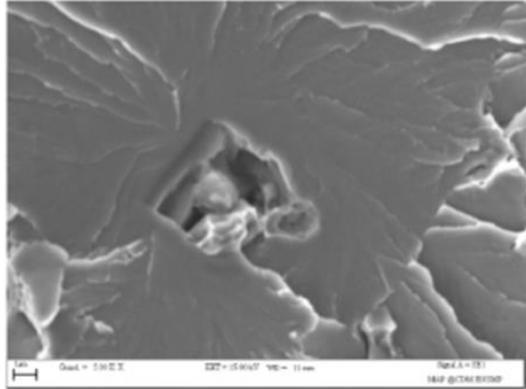
$$\dot{\rho}_m = \frac{\kappa \xi}{r_0} \rho_{irr}(t) \dot{\gamma}$$

affects gamma-dot in eq. (2)

☞ Interaction means dislocation pinning, which subsequently act as source of mobile dislocation for their further generation.

☞ This mechanism/term is defect-size dependent (irradiation temperature)

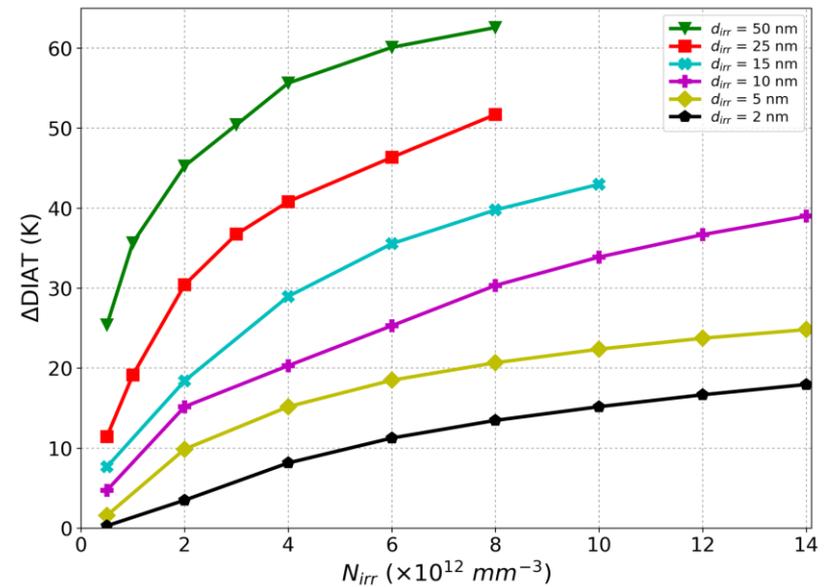
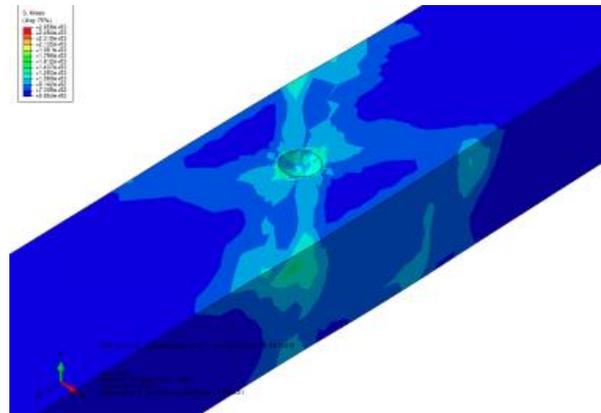
Preliminary results: FEM model



To predict stress field near fracture initiator and its dose-dependent evolutions

☞ Link with DD calculations: Δ DIAT predictor

☞ Link with MIBF model

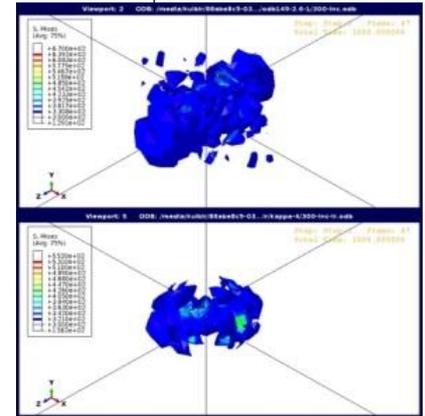
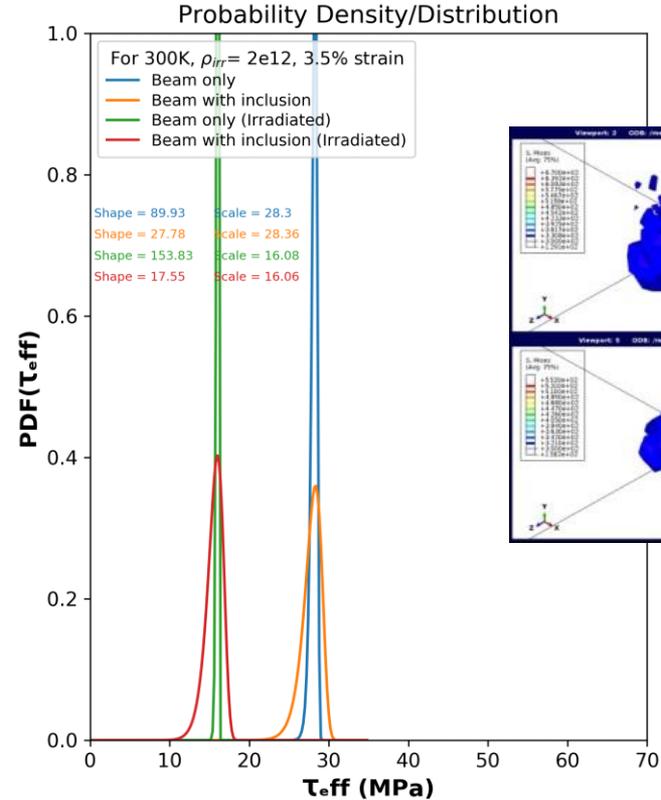
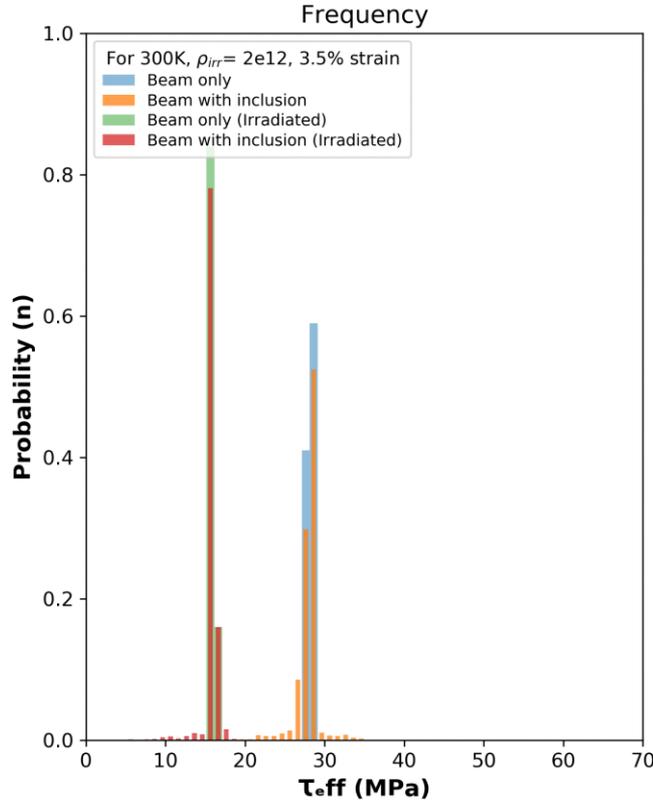


Stress field near fracture initiator:
Weibull statistics description

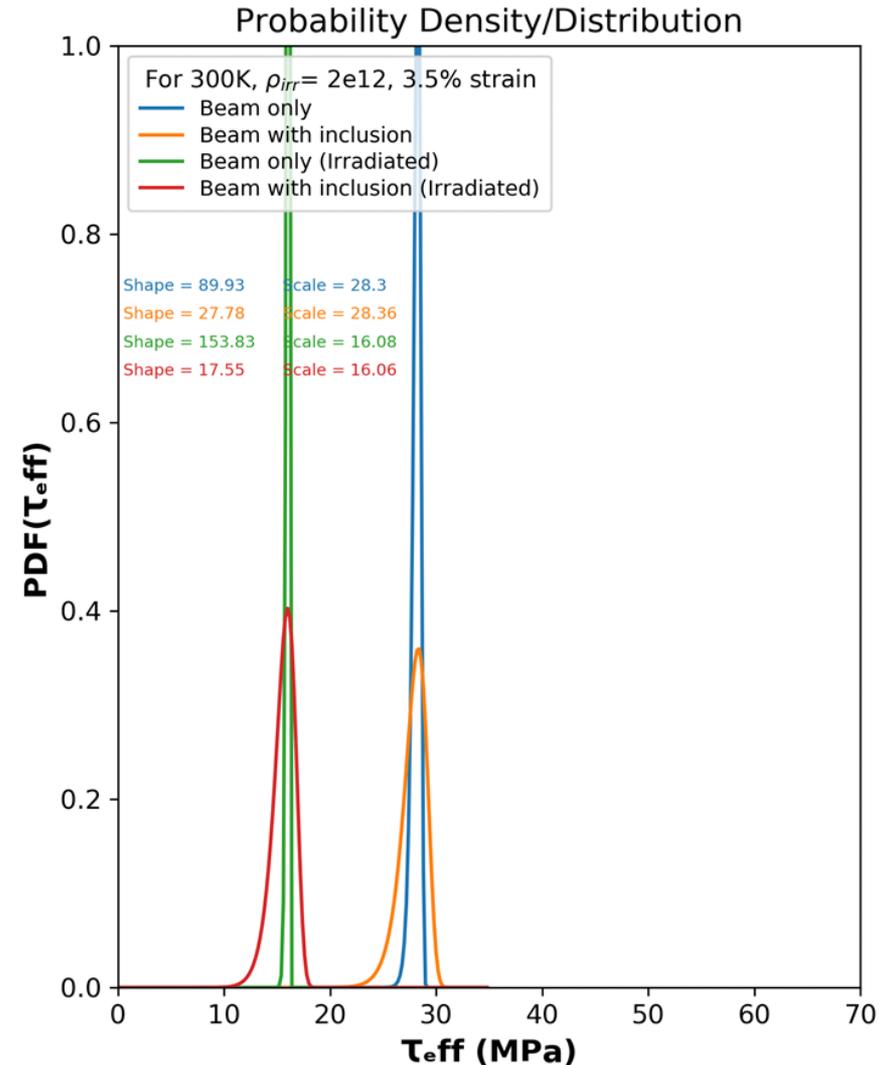
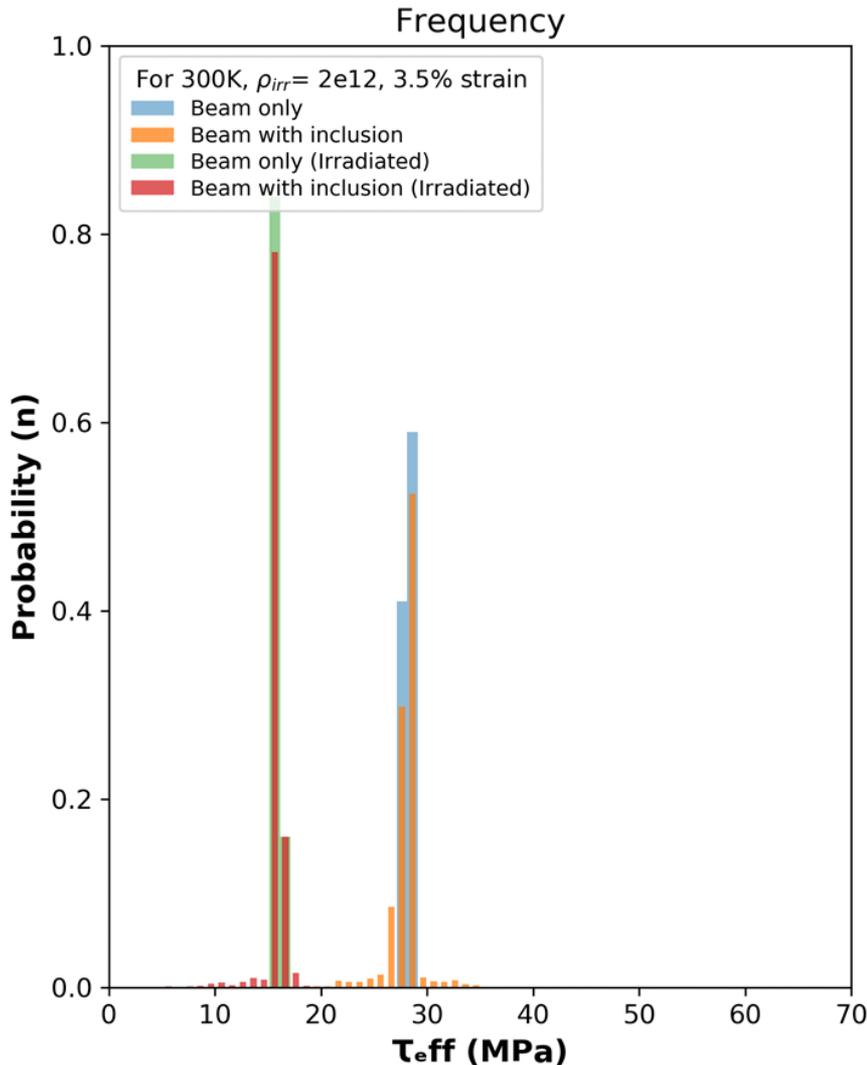
$$f(\tau_{eff}) = \frac{\beta}{\eta} \left(\frac{\tau_{eff} - \gamma}{\eta} \right)^{\beta-1} \exp - \left(\frac{\tau_{eff} - \gamma}{\eta} \right)^{\beta}$$

Scale Parameter \leftarrow η \leftarrow Position Parameter

Shape Parameter \leftarrow β



Irradiation defect size - 15 nm

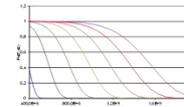
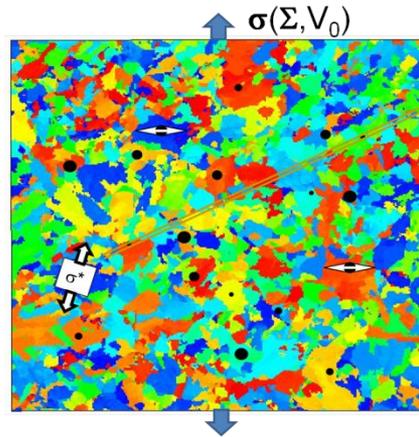


Preliminary results: link with MIBF model

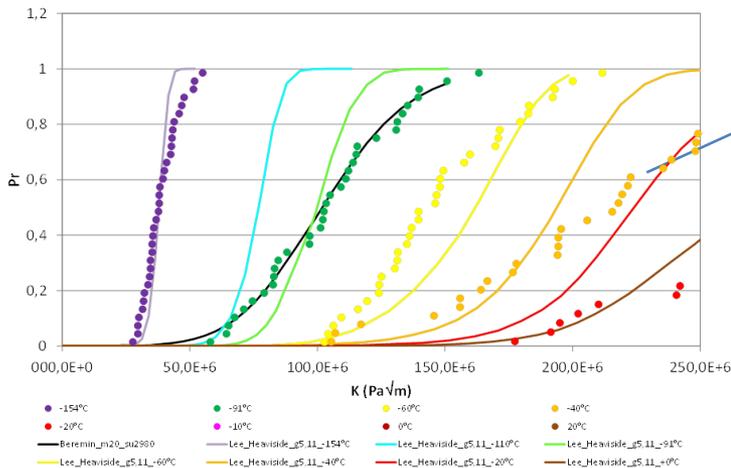


Ongoing: to compare $\Delta DIAT$ and $\Delta DBTT$ based on MIBF prediction

RPV steel microstructure
 \Rightarrow local stress distribution σ^* inside V_0 .



$+\Delta\sigma$ or dose-dependent change of Weibull grain stress distribution parameters



$$P_f(V_p, \Sigma) = 1 - \exp \left(\int_{V_p} \ln(1 - P_f(V_0, \sigma)) \frac{dV}{V_0} \right)$$

Example: as-received (0 dpa) conditions
 Solid line: without grain plasticity
 Solid symbols: accounting for grain plasticity

- In presence of disperse defect populations:
 - «Weakest link» fracture model framework: toughness level is controlled by the **plastic zone size « a_0 »**, near the BF initiators (particles or GB)
 - Plastic zone size « a_0 » is **dose-dependent** and scales with the **apparent (screw) dislocation mobility**
 - Apparent dislocation mobility depends on dispersed defect populations and can be estimated using the **statistical Δ DIAT concept**
 - Calculated Δ DIAT levels are comparable to DBT transition shifts, for a given disperse defect microstructure (N , D)
 - DD and Δ DIAT approach used in support of crystal plasticity calculation framework
 - Corresponding dose-dependent stress distributions to feed MIBF model, predicting DBT shift and level

- Perspectives:
 - To apply Δ DIAT method to a broader range of materials and irradiation conditions
 - To predict dose-dependent evolutions of upper shelf level